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Low-Power Bandgap Reference Design

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Background

□A bandgap reference (BGR) circuit produces a constant voltage regardless of power supply variations, temperature changes, or circuit loadings.

□In order to meet the demand for reduced power consumption of circuit systems in recent years, the low-power BGR has become a major challenge.

The supply voltage is limited by $V_{EB}+V_{DS}$. Since M_{1-3} should operate in saturation region, V_{EB} should be

Introduction

□ The traditional BGR

I_{R2} is a PTAT current. $(I_{R2} = \frac{\Delta V_{EB}}{R_{2}})$ I_{R3} is a CTAT current. $(I_{R3} = \frac{V_{EB1}}{R_2})$ $I_{R4} = I_{R2} + I_{R3} = \frac{\Delta V_{EB}}{R_2} + \frac{V_{EB1}}{R_3}$ $\mathbf{V}_{\text{REF}} = \mathbf{I}_{\text{R4}} \times \mathbf{R}_4 = \frac{R_4}{R_2} \Delta \mathbf{V}_{\text{EB}} + \frac{R_4}{R_3} \mathbf{V}_{\text{EB1}}$



The BJT current is controlled well by resistor ratio so as to let the BJT mismatch be fixed even for a lower biascurrent range.

Since the supply voltage is limited mainly by V_{ER} , additional current paths are added to reduce the current on BJT, which reduce VEB at the same time.

□However, using an extra opamp results in higher

□We will develop new BGR architecture without using an extra opamp to reduce the current on BJTs and

The new BGR circuit will be applied in some lowpower and low-supply-voltage applications, such as low-power energy-harvesting systems and thermal-



□However, the extra operational amplifier (OP2) may increase power consumption and area, which degrades the system performance.

sensors.



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- [2]B. Yousefzadeh, S. Heidary Shalmany and K. A. A. Makinwa, "A BJT-Based Temperature-to-Digital Converter With ± 60 mK (3σ) Inaccuracy From -55 °C to +125 °C in 0.16-µm CMOS," in IEEE Journal of Solid-State Circuits, pp. 1044-1052, April 2017.